

Green ZXMS6004DGQ 60V N-CHANNEL SELF PROTECTED ENHANCEMENT MODE INTELLIFET MOSFET

#### **Product Summary**

- Continuous Drain Source Voltage: V<sub>DS</sub>= 60V
- On-State Resistance: 500mΩ
- Nominal Load Current (V<sub>IN</sub> = 5V): 1.3A
- Clamping Energy: 490mJ

#### Description

The ZXMS6004DGQ is a self protected low side IntelliFET<sup>™</sup> MOSFET with logic level input. It integrates over-temperature, overcurrent, over-voltage (active clamp) and ESD protected logic level functionality. The ZXMS6004DGQ is ideal as a general purpose switch driven from 3.3V or 5V microcontrollers in harsh environments where standard MOSFETs are not rugged enough.

## **Applications**

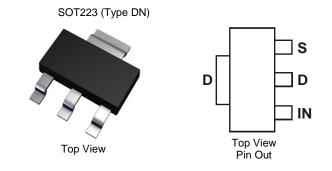
- Especially Suited for Loads with a High In-Rush Current such as Lamps and Motors
- All Types of Resistive, Inductive and Capacitive Loads in Switching Applications
- µC Compatible Power Switch for 12V and 24V DC Applications
- Automotive Rated
- Replaces Electromechanical Relays and Discrete Circuits
- Linear Mode Capability the current-limiting protection circuitry is designed to de-activate at low V<sub>DS</sub> to minimize on state power dissipation. The maximum DC operating current is therefore determined by the thermal capability of the package/board combination, rather than by the protection circuitry. This does not compromise the product's ability to self-protect at low V<sub>DS</sub>.

#### **Features and Benefits**

- Compact High Power Dissipation Package
- Low Input Current
- Logic Level Input (3.3V and 5V)
- Short Circuit Protection with Auto Restart
- Over Voltage Protection (Active Clamp)
- Thermal Shutdown with Auto Restart
- Over-Current Protection
- Input Protection (ESD)
- High Continuous Current Rating
- Lead-Free Finish; RoHS Compliant (Note 1 & 2)
- Halogen and Antimony Free. "Green" Device (Note 3)
- Qualified to AEC-Q101 Standards for High Reliability
- PPAP Capable (Note 4)

### **Mechanical Data**

- Case: SOT223 (Type DN)
- Case Material: Molded Plastic, "Green" Molding Compound UL Flammability Classification Rating 94V-0
- Moisture Sensitivity: Level 1 per J-STD-020
- Terminals: Matte Tin Finish @3
- Weight: 0.112 grams (Approximate)



#### Ordering Information (Note 5)

	,			
Product	Marking	Reel Size (inches)	Tape Width (mm)	Quantity per Reel
ZXMS6004DGQTA	ZXMS6004D	7	12	1,000

Notes: 1. EU Directive 2002/95/EC (RoHS), 2011/65/EU (RoHS 2) & 2015/863/EU (RoHS 3) compliant. All applicable RoHS exemptions applied.

2. See http://www.diodes.com/quality/lead\_free/ for more information about Diodes Incorporated's definitions of Halogen- and Antimony-free, "Green" and Lead-free.

3. Halogen- and Antimony-free "Green" products are defined as those which contain <900ppm bromine, <900ppm chlorine (<1500ppm total Br + Cl) and <1000ppm antimony compounds.

4. Automotive products are AEC-Q101 qualified and are PPAP capable. Refer to https://www.diodes.com/quality/.

5. For packaging details, go to our website at https://www.diodes.com/design/support/packaging/diodes-packaging/

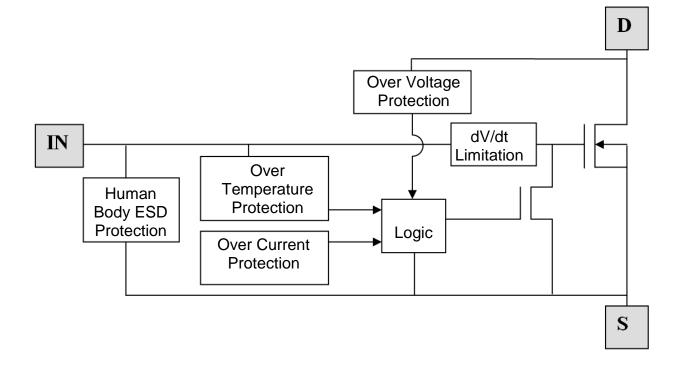
### **Marking Information**



ZXMS6004D = Product Type Marking Code YWW = Date Code Marking Y or  $\overline{Y}$  = Last Digit of Year (ex: 8 = 2018) WW or  $\overline{WW}$  = Week Code (01 to 53)



## **Functional Block Diagram**



## Absolute Maximum Ratings (@T<sub>A</sub> = +25°C, unless otherwise stated.)

Characteristic	Symbol	Value	Unit
Continuous Drain-Source Voltage	V <sub>DS</sub>	60	V
Drain-Source Voltage for Short Circuit Protection	V <sub>DS(SC)</sub>	36	V
Continuous Input Voltage	VIN	-0.5 to +6	V
Continuous Input Current @-0.2V $\leq$ V <sub>IN</sub> $\leq$ 6V Continuous Input Current @V <sub>IN</sub> < -0.2V or V <sub>IN</sub> > 6V	l <sub>IN</sub>	No Limit   I <sub>IN</sub>   ≤2	mA
Pulsed Drain Current @V <sub>IN</sub> = 3.3V	I <sub>DM</sub>	2	А
Pulsed Drain Current @V <sub>IN</sub> = 5V	I <sub>DM</sub>	2.5	А
Continuous Source Current (Body Diode) (Note 6)	I <sub>S</sub>	1	А
Pulsed Source Current (Body Diode)	I <sub>SM</sub>	5	А
Unclamped Single Pulse Inductive Energy, $T_J = +25^{\circ}C$ , $I_D = 0.5A$ , $V_{DD} = 24V$	Eas	490	mJ
Electrostatic Discharge (Human Body Model)	V <sub>ESD</sub>	4000	V
Charged Device Model	V <sub>CDM</sub>	1000	V

## **Thermal Resistance**

Characteristic	Symbol	Value	Unit
Power Dissipation at $T_A = +25^{\circ}C$ (Note 6) Linear Derating Factor	PD	1.3 10.4	W mW/°C
Power Dissipation at $T_A = +25^{\circ}C$ (Note 7) Linear Derating Factor	PD	3.0 24	W mW/°C
Thermal Resistance, Junction to Ambient (Note 6)	R <sub>0JA</sub>	96	°C/W
Thermal Resistance, Junction to Ambient (Note 7)	R <sub>0JA</sub>	42	°C/W
Thermal Resistance, Junction to Case (Note 8)	R <sub>0JC</sub>	12	°C/W
Operating Temperature Range	TJ	-40 to +150	°C
Storage Temperature Range	T <sub>STG</sub>	-55 to +150	°C

7. For a device surface mounted on 50mm x 50mm single sided 2oz weight copper on 1.6mm FR-4 board, in still air conditions. 8. Thermal resistance between junction and the mounting surfaces of drain and source pins.

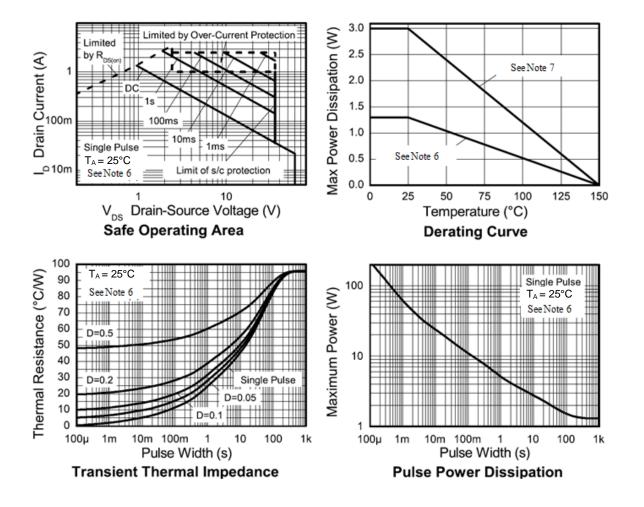


## **Recommended Operating Conditions**

The ZXMS6004DGQ is optimized for use with  $\mu$ C operating from 3.3V and 5V supplies.

Characteristic	Symbol	Min	Max	Unit
Input Voltage Range	V <sub>IN</sub>	0	5.5	V
Ambient Temperature Range	T <sub>A</sub>	-40	+125	°C
High Level Input Voltage for MOSFET to be on	V <sub>IH</sub>	3	5.5	V
Low Level Input Voltage for MOSFET to be off	V <sub>IL</sub>	0	0.7	V
Peripheral Supply Voltage (Voltage to Which Load is Referred)	VP	0	36	V

## **Thermal Characteristics**





## Electrical Characteristics (@T<sub>A</sub> = +25°C, unless otherwise stated.)

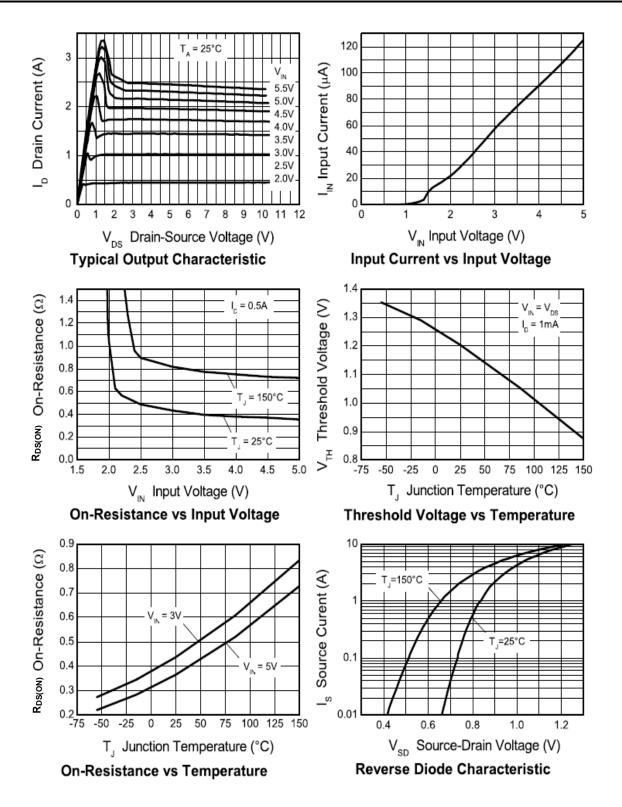
Characteristic	Symbol	Min	Тур	Max	Unit	Test Condition
Static Characteristics	• •				•	÷
Drain-Source Clamp Voltage	V <sub>DS(AZ)</sub>	60	65	70	V	$I_D = 10 \text{mA}$
Off State Drain Current	IDSS	-	-	0.5	μA	$V_{DS} = 12V, V_{IN} = 0V$
On State Drain Current		-	-	1		$V_{DS} = 36V, V_{IN} = 0V$
Input Threshold Voltage	V <sub>IN(TH)</sub>	0.7	1.2	1.5	V	$V_{DS} = V_{GS}, I_D = 1mA$
Input Current		-	60	100	μA	$V_{IN} = 3V$
Input Current	lin	-	120	200		$V_{IN} = 5V$
Input Current While Over Temperature Active	-	-	-	400	μA	$V_{IN} = 5V$
Static Drain-Source On-State Resistance	R <sub>DS(ON)</sub>	-	400	600		$V_{IN} = 3V, I_D = 0.5A$
Static Drain-Source On-State Resistance		-	350	500	mΩ	$V_{IN} = 5V, I_D = 0.5A$
Continuous Drain Current (Nata C)	ID	0.9	_	-	- A	V <sub>IN</sub> = 3V; T <sub>A</sub> = +25°C
Continuous Drain Current (Note 6)		1.0	-	-		V <sub>IN</sub> = 5V; T <sub>A</sub> = +25°C
Continuous Drain Current (Nata 7)		1.2	-	-		V <sub>IN</sub> = 3V; T <sub>A</sub> = +25°C
Continuous Drain Current (Note 7)		1.3	_	-		V <sub>IN</sub> = 5V; T <sub>A</sub> = +25°C
Current Limit (Note 0)	I <sub>D(LIM)</sub>	0.7	1.7	-	A	$V_{IN} = 3V$
Current Limit (Note 9)		1	2.2	_		$V_{IN} = 5V$
Dynamic Characteristics						
Turn On Delay Time	t <sub>D(ON)</sub>	-	5	-		
Rise Time	t <sub>R</sub>	-	10	-	1	$V_{DD} = 12V, I_D = 0.5A,$
Turn Off Delay Time	t <sub>D(OFF)</sub>	-	45	-	μs	$V_{GS} = 5V$
Fall Time	f <sub>F</sub>	-	15	-	1	
Over-Temperature Protection						
Thermal Overload Trip Temperature (Note 10)	T <sub>JT</sub>	+150	+175	-	°C	-
Thermal Hysteresis (Note 10)	-	_	+10	-	°C	-

Notes: 9. The drain current is restricted only when the device is in saturation (see graph 'typical output characteristic'). This allows the device to be used in the fully on state without interference from the current limit. The device is fully protected at all drain currents, as the low power dissipation generated outside saturation makes current limit unnecessary. 10. Over-temperature protection is designed to prevent device destruction under fault conditions. Fault conditions are considered as "outside" normal

operating range, so this part is not designed to withstand over-temperature for extended periods.

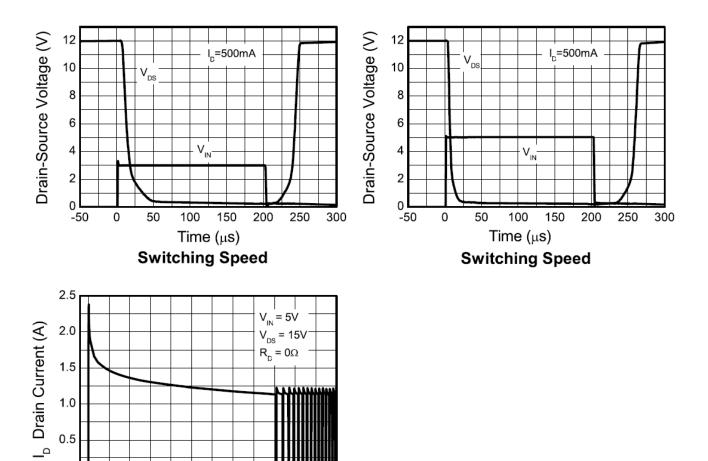


## **Typical Characteristics**





## Typical Characteristics (Cont.)



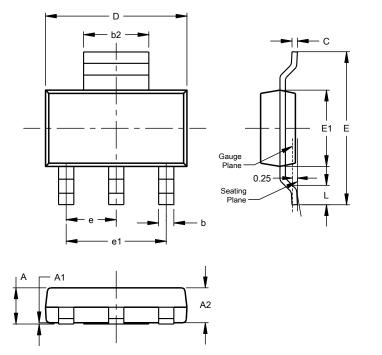
0.0 0 25 50 75 100 125 150 Time (ms) Typical Short Circuit Protection



### **Package Outline Dimensions**

Please see http://www.diodes.com/package-outlines.html for the latest version.

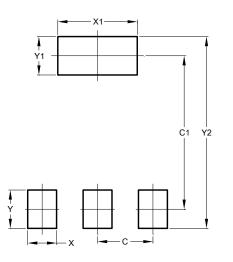
#### SOT223 (Type DN)



SOT223 (Type DN)					
חווס	IVIIN	Max	Тур		
Α		1.70			
A1	0.01	0.15			
A2	1.50	1.68	1.60		
b	0.60	0.80	0.70		
b2	2.90	3.10			
C	0.20	0.32			
D	6.30	6.70			
ш	6.70	7.30			
E1	3.30	3.70			
e			2.30		
e1			4.60		
L	0.85				
All [	Dimens	ions in	mm		

# Suggested Pad Layout

Please see http://www.diodes.com/package-outlines.html for the latest version.



#### SOT223 (Type DN)

Dimensions	Value (in mm)	
С	2.30	
C1	6.40	
Х	1.20	
X1	3.30	
Y	1.60	
Y1	1.60	
Y2	8.00	



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